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PATENT

I hereby certify that on the date specified below, this correspondence is being deposited with the United States Postal Service as first-class mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

September 25, 2006

Date

abeggs

Alexandra Beggs

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Kie Y. Ahn and Leonard Forbes      Attorney Docket No.: 500466.04  
Patent No. : US 6,953,375 B2      Serial No. : 10/813,204  
Issue Date : October 11, 2005      Filed : March 29, 2004  
Title : MANUFACTURING METHOD OF A FIELD EMISSION DISPLAY HAVING  
POROUS SILICON DIOXIDE INSULATING LAYER

REQUEST FOR CERTIFICATE OF CORRECTION

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**Certificate**  
OCT 06 2006  
**of Correction**

Sir:

A Certificate of Correction under 35 U.S.C. § 254 is respectfully requested for the above-identified patent in order to correct Patent and Trademark Office errors made during the printing of the patent. The changes in the patent needed to correct the errors are as follows:

| <u>Column, Line</u>                                   | <u>Reads</u>                       | <u>Should Read</u>                 |
|---|------------------------------------|------------------------------------|
| Item (56), Other Publications,<br>Stevenson Reference | "of SiO <sub>2</sub> , Films Over" | --of SiO <sub>2</sub> Films Over-- |
| Item (56), Other Publications,<br>Vaudaine Reference  | "technical digest of IEDM 91,"     | --Technical Digest of IEDM 91,--   |
| Column 4, Line 32                                     | "FIG. 3), having a"                | --FIG. 3) having a--               |

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|                        |  |   |
|------------------------|--|---|
| Column 5, Line 18      | “ca. 10 <sup>2-103</sup> ,”                          | --ca. 10 <sup>2</sup> -10 <sup>3</sup> --                 |
| Column 6, Line 35      | “Mater. Sci. 32, (1997),”                            | --Mater. Sci. 32 (1997),--                                |
| Column 7, Line 23      | “69(7), (1996),”                                     | --69(7) (1996)--  |
| Column 7, Line 38      | “Silicon at low”                                     | --Silicon at Low--  |
| Column 7, Line 53      | “Part 1, Vol. 36,”                                   | --Part I, Vol. 36,--                                      |
| Column 9, Lines 24-25  | “comprises chemical-mechanical polishing the porous” | --comprises chemical-mechanical polishing of the porous-- |
| Column 10, Lines 26-27 | “comprises chemical-mechanical polishing the porous” | --comprises chemical-mechanical polishing of the porous-- |
| Column 10, Line 41     | “act of fanning”                                     | --act of forming--  |
| Column 12, Lines 10-11 | “comprises chemical-mechanical polishing the”        | --comprises chemical-mechanical polishing of the--        |

The above errors for which correction is requested under 35 U.S.C. § 254 were made in the printing of the patent or in the original application. The errors are considered sufficiently important to justify the processing of a Certificate of Correction under 35 U.S.C. § 254. A Form PTO-1050, in duplicate, is enclosed herewith.

The Commissioner is hereby authorized to charge payment of any fees associated with this communication to Deposit Account No. 50-1266. A duplicate copy of this sheet is enclosed.

OCT 11 2006

Favorable consideration of this Request is respectfully requested.

Respectfully submitted,

Date:

Sept. 21, 2006

By:

Edward W. Bulchis

Edward W. Bulchis, Reg. No. 26,847

Customer No. 27,076

Dorsey & Whitney LLP

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Enclosures:

Postcard

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DATED : October 11, 2005  
INVENTOR(S) : Kie Y. Ahn and Leonard Forbes

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Patent No. US 6,953,375 B2

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